

isc Silicon PNP Power Transistor

MJD253

DESCRIPTION

- High DC Current Gain–
: $h_{FE} = 40(\text{Min}) @ I_C = -0.2 \text{ A}$
- Low Collector Saturation Voltage–
: $V_{CE(\text{sat})} = -0.3\text{V}(\text{Max.}) @ I_C = -0.5 \text{ A}$
- Complement to the NPN MJD243
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

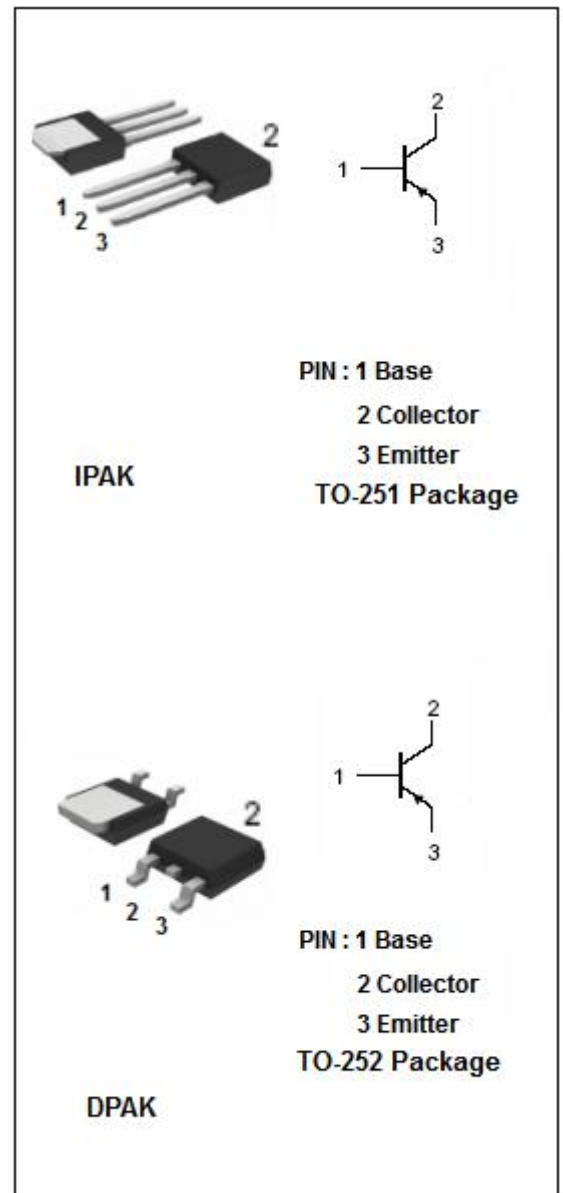
- Designed for low voltage, low -power ,high-gain audio amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-Peak	-8	A
I_B	Base Current	-1	A
P_C	Collector Power Dissipation $T_a=25^\circ\text{C}$	1.4	W
	Collector Power Dissipation $T_C=25^\circ\text{C}$	12.5	
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	10	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	89.3	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

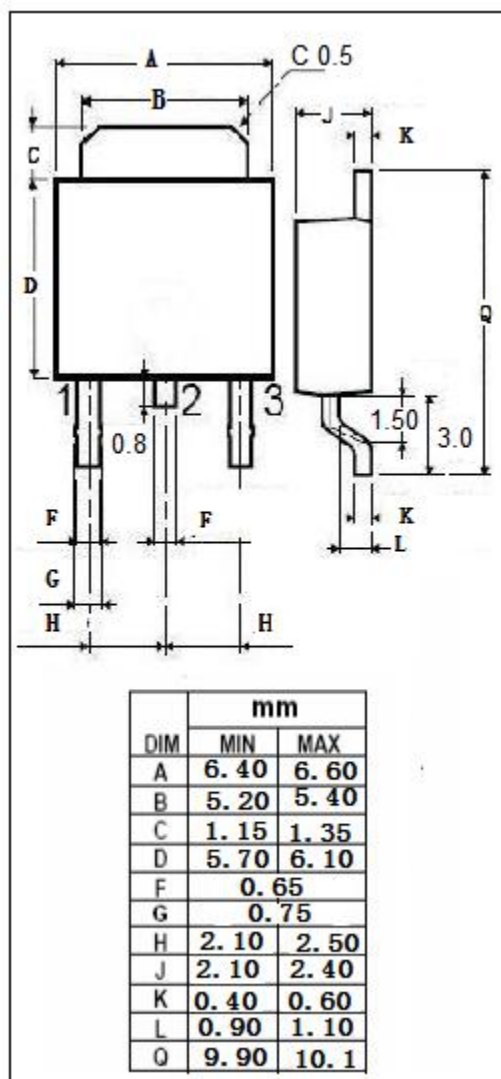
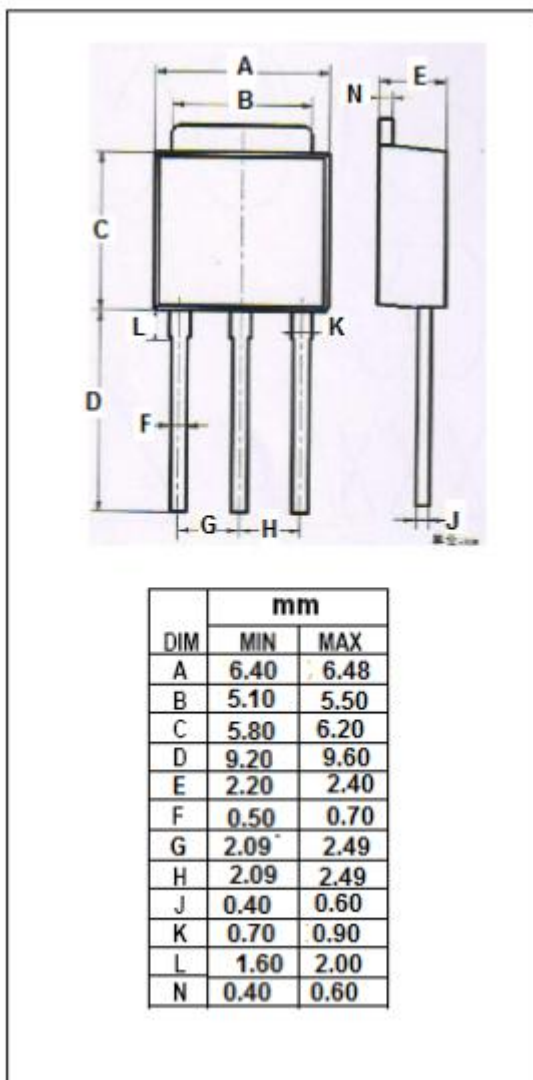
 $T_c = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -10\text{mA}; I_B = 0$	-100		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -0.5\text{A}; I_B = -50\text{mA}$		-0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -1\text{A}; I_B = -0.1\text{A}$		-0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$		-1.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -0.5\text{A}; V_{CE} = -1\text{V}$		-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -100\text{V}; I_E = 0$ $V_{CB} = -100\text{V}; I_E = 0; T_c = 125^\circ\text{C}$		-0.1 -0.1	μA mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -7\text{V}; I_C = 0$		-0.1	μA
h_{FE-1}	DC Current Gain	$I_C = -0.2\text{A}; V_{CE} = -1\text{V}$	40	180	
h_{FE-2}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -1\text{V}$	15		
f_T	Current-Gain—Bandwidth Product	$I_C = -0.1\text{A}; V_{CE} = -10\text{V}; f_{test} = 10\text{MHz}$	40		MHz
C_{OB}	Collector Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f_{test} = 0.1\text{MHz}$	40		pF

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Outline Drawing



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